



168-Ball LPDDR2 SDRAM Addendum Features

Table 1: Configuration Addressing – Single-Channel Package (Continued)

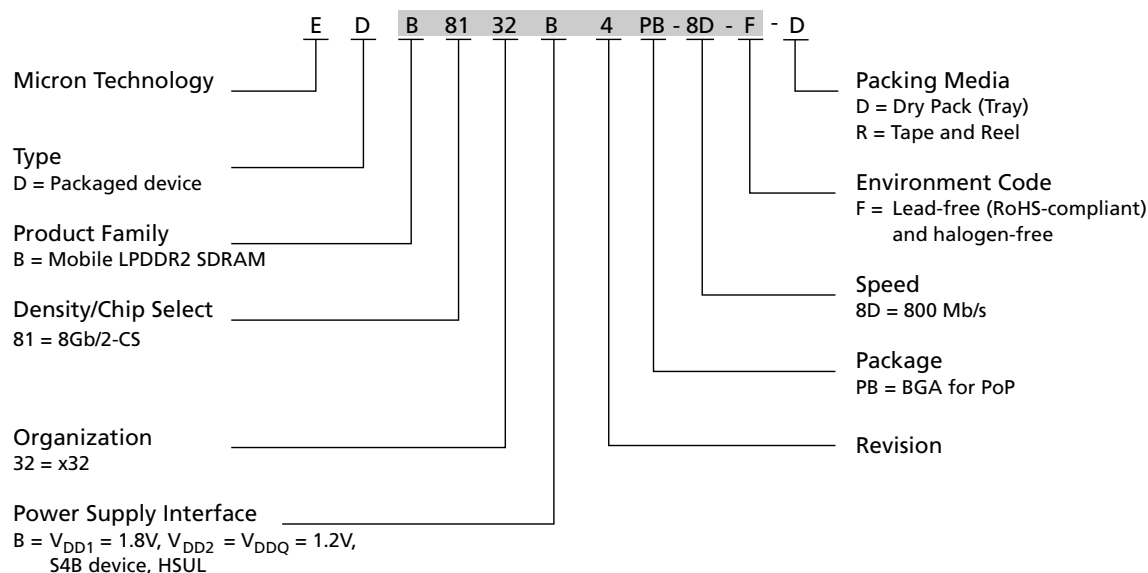
Architecture	256 Meg x 32
Row addressing	16K A[13:0]
Column addressing	2K A[10:0]

Table 2: Key Timing Parameters

Speed Grade	Clock Rate (MHz)	Data Rate (Mb/s/pin)	WRITE Latency	READ Latency
8D	400	800	3	6

Table 3: Part Number Description

Part Number	Total Density	Configuration	Ranks	Channels	Package Size	Ball Pitch
EDB8132B4PB-8D-F-R, EDB8132B4PB-8D-F-D	8Gb	256 Meg x 32	1	1	12mm x 12mm (0.80mm MAX height)	0.50mm

Figure 1: Marketing Part Number Chart


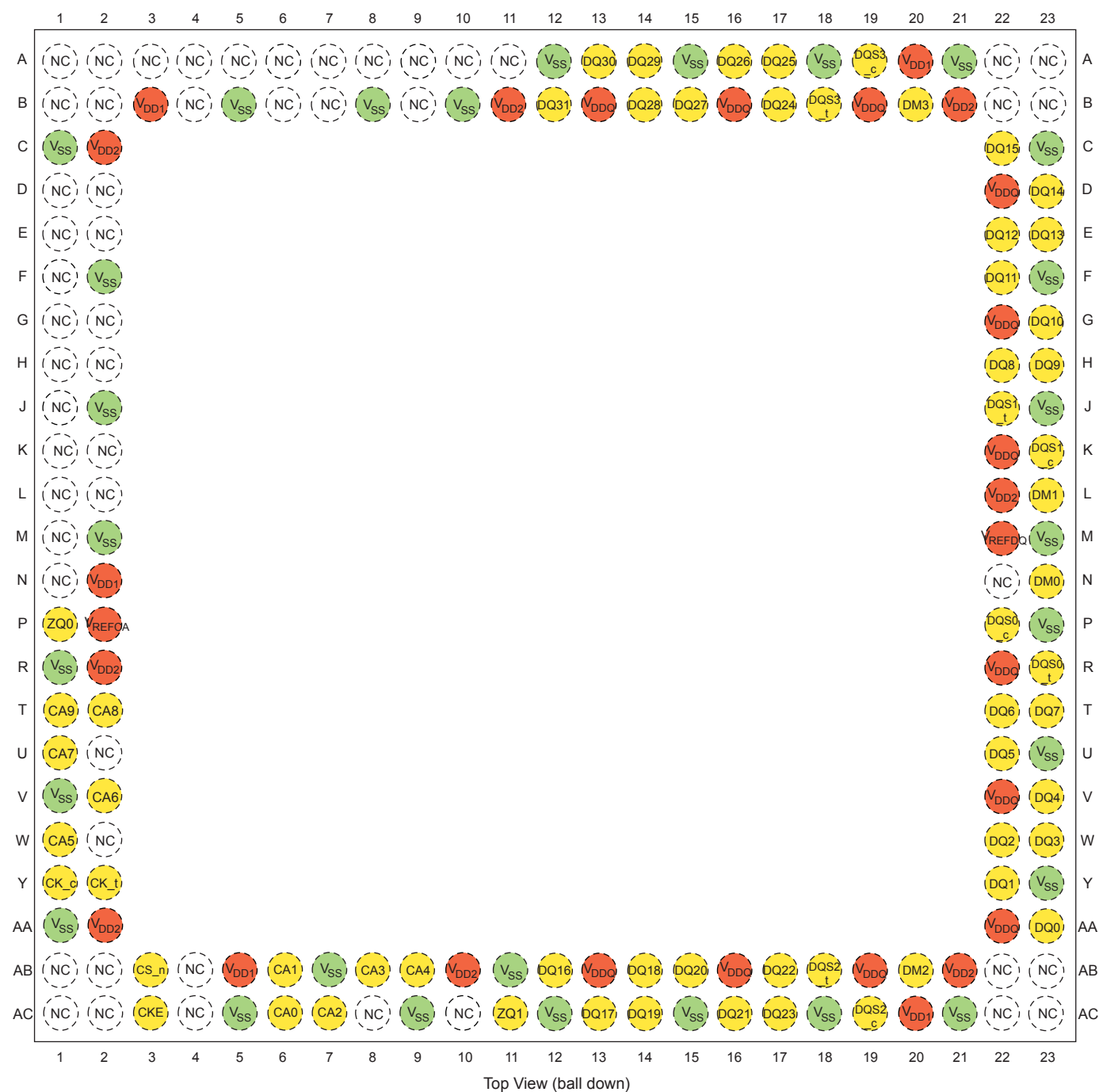
Note: 1. The characters highlighted in gray indicate the physical part marking found on the device.



168-Ball LPDDR2 SDRAM Addendum Ball Assignments

Ball Assignments

Figure 2: 168-Ball PoP Single-Channel FBGA – 2 x 4Gb Die, 12mm x 12mm





168-Ball LPDDR2 SDRAM Addendum Ball Descriptions

Ball Descriptions

The ball/pad description table below is a comprehensive list of signals for the device family. All signals listed may not be supported on this device. See Ball Assignments for information specific to this device.

Table 4: Ball/Pad Descriptions

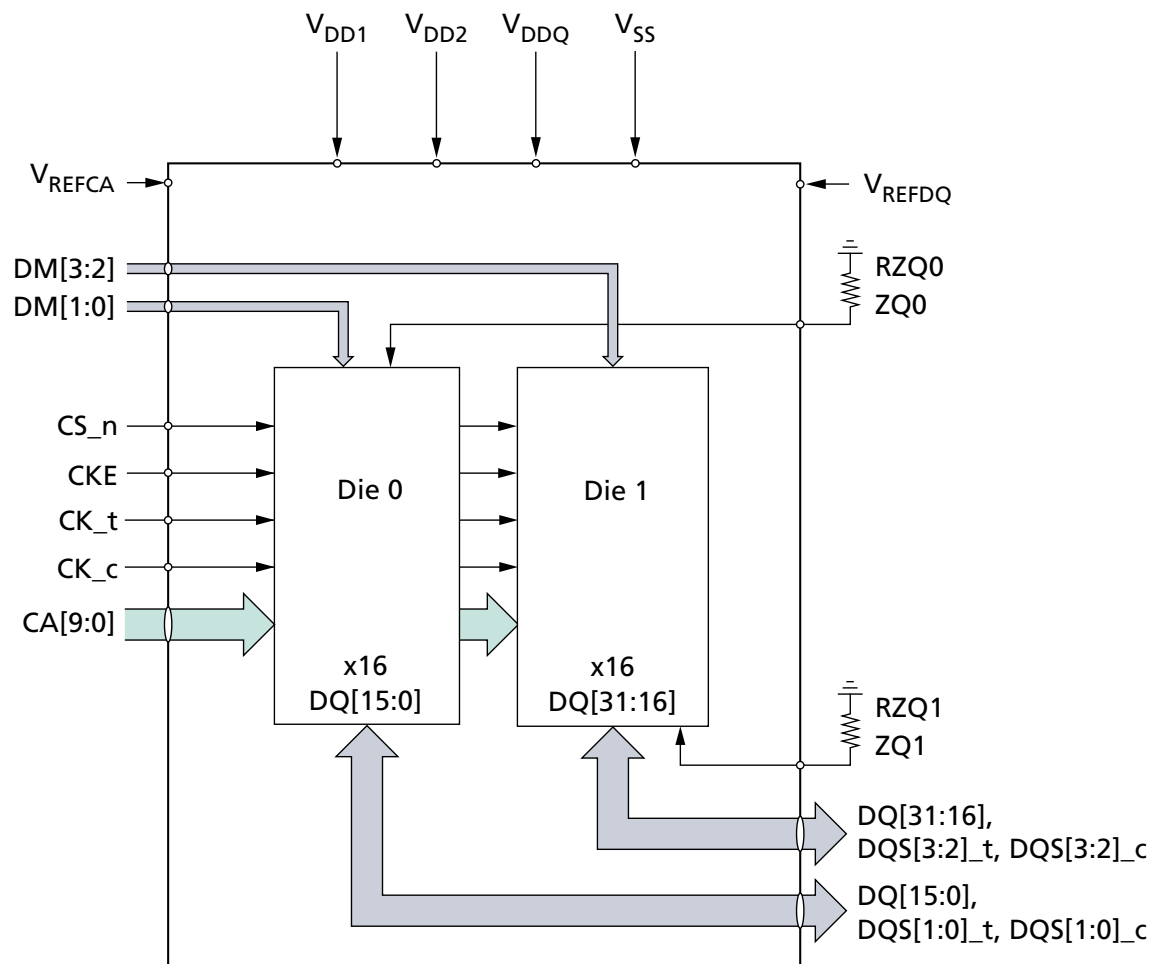
Symbol	Type	Description
CA[9:0]	Input	Command/address inputs: Provide the command and address inputs according to the command truth table.
CK_t, CK_c	Input	Clock: Differential clock inputs. All CA inputs are sampled on both rising and falling edges of CK. CS and CKE inputs are sampled at the rising edge of CK. AC timings are referenced to clock.
CKE	Input	Clock enable: CKE HIGH activates and CKE LOW deactivates the internal clock signals, input buffers, and output drivers. Power-saving modes are entered and exited via CKE transitions. CKE is considered part of the command code. CKE is sampled on the rising edge of CK.
CS_n	Input	Chip select: Considered part of the command code and is sampled on the rising edge of CK.
DM[3:0]	Input	Input data mask: Input mask signal for write data. Although DM balls are input-only, the DM loading is designed to match that of DQ and DQS balls. DM[3:0] is DM for each of the four data bytes, respectively.
DQ[31:0]	I/O	Data input/output: Bidirectional data bus.
DQS[3:0]_t, DQS[3:0]_c	I/O	Data strobe: Bidirectional (used for read and write data) and complementary (DQS_t and DQS_c). It is edge-aligned output with read data and centered input with write data. DQS[3:0]_t/DQS[3:0]_c is DQS for each of the four data bytes, respectively.
V _{DDQ}	Supply	DQ power supply: Isolated on the die for improved noise immunity.
V _{SSQ}	Supply	DQ ground: Isolated on the die for improved noise immunity.
V _{DD1}	Supply	Core power: Supply 1.
V _{DD2}	Supply	Core power: Supply 2.
V _{SS}	Supply	Common ground.
V _{REFCA} , V _{REFDQ}	Supply	Reference voltage: V _{REFCA} is reference for command/address input buffers, V _{REFDQ} is reference for DQ input buffers.
ZQ[1:0]	Reference	External reference ball for output drive calibration: This ball is tied to an external 240Ω resistor (RZQ), which is tied to V _{SSQ} .
NU	–	Not usable: Do not connect.
NC	–	No connect: Not internally connected.
(NC)	–	No connect: Balls indicated as (NC) are no connects; however, they could be connected together internally.



168-Ball LPDDR2 SDRAM Addendum Package Block Diagrams

Package Block Diagrams

Figure 3: Single-Rank, Dual-Die, Single-Channel Package Block Diagram

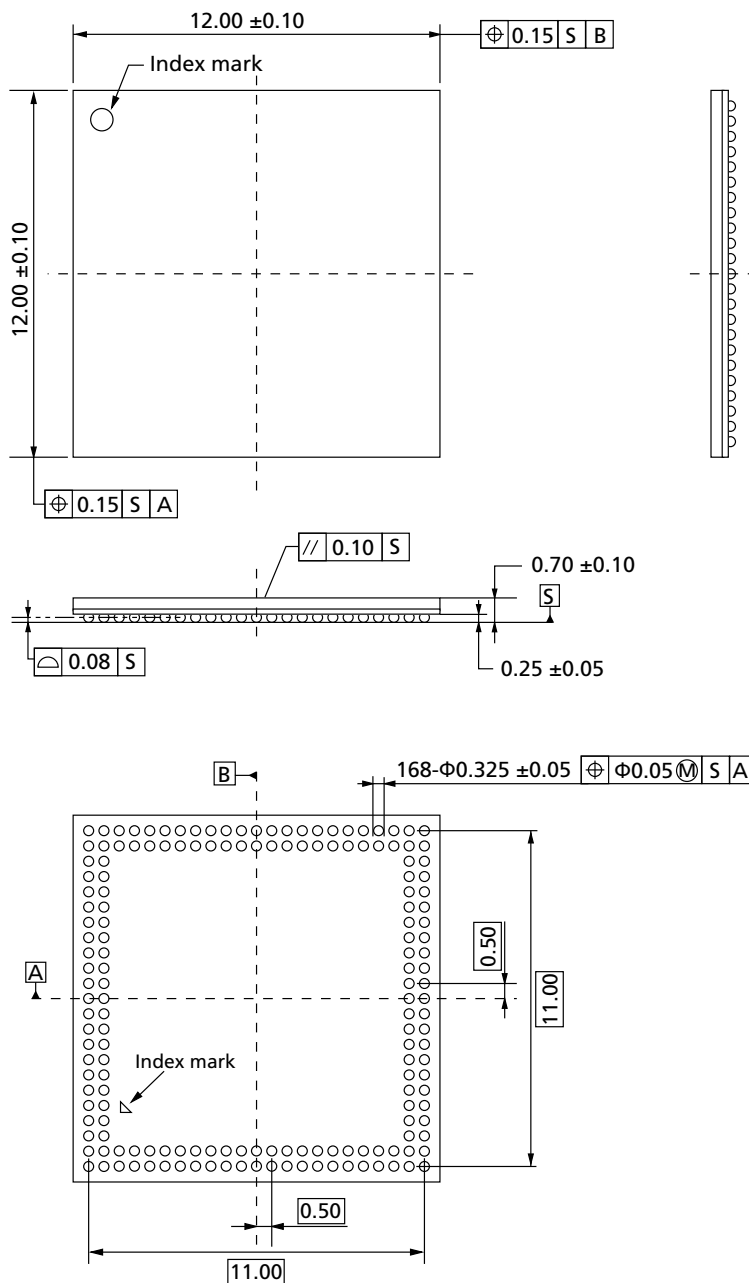




168-Ball LPDDR2 SDRAM Addendum Package Dimensions

Package Dimensions

Figure 4: 168-Ball PoP FBGA (12mm x 12mm) – EDB8132B4PB-8D-F-D/R



- Notes: 1. Package drawing: ECA-TS2-0515-02.
2. All dimensions are in millimeters.



168-Ball LPDDR2 SDRAM Addendum Revision History

Revision History

Rev. B – 7/14

- Updated resistors in Package Block Diagram

Rev. A – 4/14

- Initial release

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This data sheet contains initial characterization limits that are subject to change upon full characterization of production devices.